

Miłosz Grodzicki

List of Publications by Year in descending order

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times ranked

353
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Oxidation of GaN(0001) by low-energy ion bombardment. <i>Applied Surface Science</i> , 2014, 304, 20-23. | 6.1 | 35 |
| 2 | XPS studies on the role of arsenic incorporated into GaN. <i>Vacuum</i> , 2019, 167, 73-76. | 3.5 | 24 |
| 3 | Temperature sensitivity modulation through changing the vanadium concentration in a La ₂ MgTiO ₆ :V ⁵⁺ ,Cr ³⁺ double perovskite optical thermometer. <i>Dalton Transactions</i> , 2021, 50, 9851-9857. | 3.3 | 23 |
| 4 | Effect of annealing on Ni/GaN(0001) contact morphology. <i>Applied Surface Science</i> , 2014, 304, 24-28. | 6.1 | 20 |
| 5 | Changes of electronic properties of p-GaN(0001) surface after low-energy N ⁺ -ion bombardment. <i>Applied Surface Science</i> , 2018, 440, 547-552. | 6.1 | 20 |
| 6 | Formation of GaPd ₂ and GaPd intermetallic compounds on GaN(0001). <i>Applied Physics A: Materials Science and Processing</i> , 2015, 120, 1443-1451. | 2.3 | 18 |
| 7 | Studies of early stages of Mn/GaN(0001) interface formation using surface-sensitive techniques. <i>Vacuum</i> , 2018, 153, 12-16. | 3.5 | 17 |
| 8 | Modification of Electronic Structure of n-GaN(0001) Surface by N ⁺ -Ion Bombardment. <i>Acta Physica Polonica A</i> , 2017, 132, 351-353. | 0.5 | 14 |
| 9 | Bistable Fermi level pinning and surface photovoltage in GaN. <i>Applied Surface Science</i> , 2020, 533, 147416. | 6.1 | 13 |
| 10 | Interface formation of Al ₂ O ₃ on carbon enriched 6H-SiC(0001): Photoelectron spectroscopy studies. <i>Vacuum</i> , 2020, 177, 109345. | 3.5 | 12 |
| 11 | Surface studies of physicochemical properties of As films on GaN(0001). <i>Applied Surface Science</i> , 2019, 493, 384-388. | 6.1 | 11 |
| 12 | Interface formation of Al ₂ O ₃ on n-GaN(0001): Photoelectron spectroscopy studies. <i>Surface and Interface Analysis</i> , 2021, 53, 118-124. | 1.8 | 10 |
| 13 | Ru/GaN(0001) Interface Properties. <i>Acta Physica Polonica A</i> , 2017, 132, 354-357. | 0.5 | 10 |
| 14 | Empty core screw dislocations formed on 6H-SiC(0001) during hydrogen etching. <i>Thin Solid Films</i> , 2008, 516, 7530-7537. | 1.8 | 9 |
| 15 | Pd/GaN(0001) interface properties. <i>Materials Science-Poland</i> , 2014, 32, 252-256. | 1.0 | 9 |
| 16 | TiO thin films on GaN(0001). <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 1001-1005. | 1.5 | 9 |
| 17 | MnGa and (Mn,Ga)N-like alloy formation during annealing of Mn/GaN(0001) interface. <i>Applied Surface Science</i> , 2019, 481, 790-794. | 6.1 | 9 |
| 18 | Sb Layers on p-GaN: UPS, XPS and LEED Study. <i>Acta Physica Polonica A</i> , 2014, 126, 1128-1130. | 0.5 | 8 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Electronic properties of p-GaN co-doped with Mn by thermal process: Surface studies. <i>Surface Science</i> , 2019, 689, 121460. | 1.9 | 8 |
| 20 | As-related stability of the band gap temperature dependence in N-rich GaNAs. <i>Applied Physics Letters</i> , 2019, 115, 092106. | 3.3 | 8 |
| 21 | Formation of Excess Silicon on 6H-SiC(0001) during Hydrogen Etching. <i>Acta Physica Polonica A</i> , 2009, 116, S-82-S-85. | 0.5 | 8 |
| 22 | Properties of Bare and Thin-Film-Covered GaN(0001) Surfaces. <i>Coatings</i> , 2021, 11, 145. | 2.6 | 7 |
| 23 | Characterization of Cr/6H-SiC(0001) nano-contacts by current-sensing AFM. <i>Applied Surface Science</i> , 2009, 256, 1014-1018. | 6.1 | 5 |
| 24 | Influence of Graphite Layer on Electronic Properties of MgO/6H-SiC(0001) Interface. <i>Materials</i> , 2021, 14, 4189. | 2.9 | 5 |
| 25 | The Influence of Oxygen and Carbon Contaminants on the Valence Band of p-GaN(0001). <i>Acta Physica Polonica A</i> , 2019, 136, 585-588. | 0.5 | 5 |
| 26 | Current patterning of 6H-SiC(0001) surface by AFM. <i>Applied Surface Science</i> , 2008, 254, 4332-4335. | 6.1 | 4 |
| 27 | Thermal stability of LiF thin films on 6H-SiC(0001) surface. <i>Vacuum</i> , 2009, 84, 622-624. | 3.5 | 4 |
| 28 | Impact of surface photovoltage on photoemission from Ni/p-GaN. <i>Applied Surface Science</i> , 2020, 512, 145643. | 6.1 | 4 |
| 29 | Au(100) as a Template for Pentacene Monolayer. <i>Molecules</i> , 2021, 26, 2393. | 3.8 | 4 |
| 30 | Electronic Properties of Structures Containing Films of Alq3 and LiBr Deposited on Si(111) Crystal. <i>Acta Physica Polonica A</i> , 2017, 132, 357-360. | 0.5 | 4 |
| 31 | Detailed surface studies on the reduction of Al incorporation into AlGaN grown by molecular beam epitaxy in the Ga-droplet regime. <i>Vacuum</i> , 2022, 202, 111168. | 3.5 | 4 |
| 32 | Thermal oxidation of [0001] GaN in water vapor compared with dry and wet oxidation: Oxide properties and impact on GaN. <i>Applied Surface Science</i> , 2022, 598, 153872. | 6.1 | 4 |
| 33 | Morphology and electric conductance of ultra-thin Cr contacts on 6H-SiC(0001): AFM and current-sensing AFM study. <i>Vacuum</i> , 2007, 82, 364-371. | 3.5 | 3 |
| 34 | AFM studies of pits formation on KBr(1 0 0) during its dissolution by water. <i>Materials Science-Poland</i> , 2016, 34, 863-867. | 1.0 | 3 |
| 35 | Physicochemical properties of the Sb/p-SiC interface. <i>Vacuum</i> , 2017, 146, 216-220. | 3.5 | 3 |
| 36 | Properties of Thin Film-Covered GaN(0001) Surfaces. , 0, , . | | 3 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 37 | Growth and properties of the GaN cap layer strongly influenced by the composition of the underlying AlGa _N . <i>Materials Science in Semiconductor Processing</i> , 2021, 136, 106125. | 4.0 | 3 |
| 38 | Topography of thin films containing Ni-Ga intermetallic compounds formed on GaN(0001). <i>Copernican Letters</i> , 0, 7, 1. | 0.0 | 3 |
| 39 | Interfacial Polarization of Thin Alq ₃ , Gaq ₃ , and Erq ₃ Films on GaN(0001). <i>Materials</i> , 2022, 15, 1671. | 2.9 | 3 |
| 40 | AFM/STM Modification of Thin Sb Films on 6H-SiC(0001). <i>Acta Physica Polonica A</i> , 2014, 126, 1131-1133. | 0.5 | 2 |
| 41 | Influence of ionic interfacial layers on electronic properties of Alq ₃ /Si(100) interface. <i>Surface and Interface Analysis</i> , 2018, 50, 623-627. | 1.8 | 2 |
| 42 | Electronic system for the complex measurement of a Wilberforce pendulum. <i>European Journal of Physics</i> , 2018, 39, 035804. | 0.6 | 2 |
| 43 | Band engineering in nitrogen-rich AlGa _N As quaternary alloys. <i>Vacuum</i> , 2021, 189, 110240. | 3.5 | 2 |
| 44 | Influence of pulsed Al deposition on quality of Al-rich Al(Ga) _N structures grown by molecular beam epitaxy. <i>Surfaces and Interfaces</i> , 2021, 27, 101560. | 3.0 | 2 |
| 45 | PHOTOELECTRON SPECTROSCOPY STUDIES ON Al ₂ O ₃ FILMS ON p-GaN(0001). <i>Surface Review and Letters</i> , 2021, 28, 2150077. | 1.1 | 1 |
| 46 | Properties of Thin MgO Films on 6H-SiC and GaN: Photoelectron Studies. <i>Acta Physica Polonica A</i> , 2022, 141, 116-122. | 0.5 | 1 |